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Correction: Effects of Ga–Te interface layer on the potential barrier height of CdTe/GaAs heterointerface

Shouzhi Xi,^{ab} Wanqi Jie,^{*ab} Gangqiang Zha,^{*ab} Yanyan Yuan,^a Tao Wang,^{ab}
Wenhua Zhang,^c Junfa Zhu,^c Lingyan Xu,^{ab} Yadong Xu,^{ab} Jie Su,^a Hao Zhang,^{ab}
Yaxu Gu,^{ab} Jiawei Li,^a Jie Ren^{ab} and Qinghua Zhao^{ab}

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Correction for 'Effects of Ga–Te interface layer on the potential barrier height of CdTe/GaAs heterointerface' by Shouzhi Xi et al., *Phys. Chem. Chem. Phys.*, 2016, **18**, 2639–2645.

Due to a calculation error, the authors would like to replace Fig. 5 in the original article with the revised version shown below:

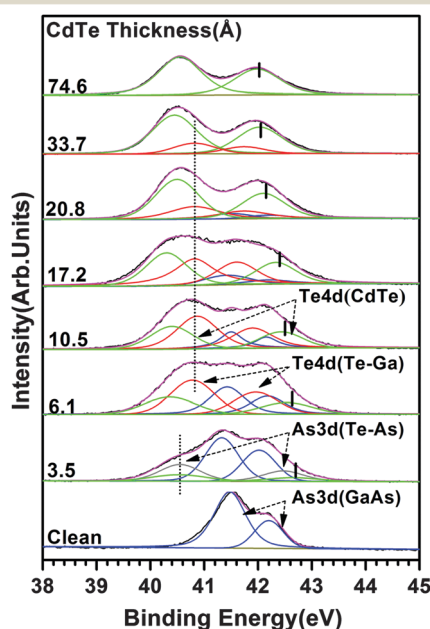


Fig. 5 Evolution of Te 4d and As 3d core levels from GaAs, CdTe, As–Te, and Ga–Te reactions at CdTe/GaAs heterointerface for various CdTe thicknesses measured by SRPES, obtained at normal emission with a photon energy of 90 eV. Black line: experiment results. Purple line: results of the best fit. Fitted with As 3d from GaAs (blue line), As 3d from Te–As reaction (gray line), Te 4d from CdTe (green line), and Te 4d from Ga–Te reaction (red line) components.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

^a State Key Laboratory of Solidification Processing, Northwestern Polytechnical University, Xi'an 710072, P. R. China. E-mail: jwq@nwpu.edu.cn, zha_gq@nwpu.edu.cn

^b Key Laboratory of Radiation Detection Materials and Devices, Ministry of Industry and Information Technology, China

^c National Synchrotron Radiation Laboratory, University of Science and Technology of China, Hefei 230029, P. R. China

